

# Takanori Asano

## List of Publications by Year in descending order

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Version: 2024-02-01

10  
papers

128  
citations

1163117

8  
h-index

1372567

10  
g-index

10  
all docs

10  
docs citations

10  
times ranked

119  
citing authors

#	ARTICLE	IF	CITATIONS
1	Formation and characterization of $\text{Ge}_{1-x}\text{Sn}_x/\text{Ge}_{1-x}\text{Sn}_x/\text{Ge}_{1-x}\text{Sn}_x$ double heterostructures with strain-controlled $\text{Ge}_{1-x}\text{Sn}_x$ layers. <i>Materials Science in Semiconductor Processing</i> , 2017, 70, 156-161.	4.0	9
2	Experimental observation of type-I energy band alignment in lattice-matched $\text{Ge}_{1-x}\text{Sn}_x/\text{Si}/\text{Ge}_{1-x}\text{Sn}_x$ heterostructures. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	23
3	Defect and dislocation structures in low-temperature-grown Ge and $\text{Ge}_{1-x}\text{Sn}_x$ epitaxial layers on Si(110) substrates. <i>Thin Solid Films</i> , 2016, 598, 72-81.	1.8	3
4	Epitaxial growth and crystalline properties of $\text{Ge}_{1-x}\text{Sn}_x$ on Ge(001) substrates. <i>Solid-State Electronics</i> , 2015, 110, 49-53.	1.4	14
5	Non-uniform depth distributions of Sn concentration induced by Sn migration and desorption during $\text{GeSnSi}$ layer formation. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	20
6	Formation of high-quality $\text{Ge}_{1-x}\text{Sn}_x$ layer on Ge(110) substrate with strain-induced confinement of stacking faults at $\text{Ge}_{1-x}\text{Sn}_x/\text{Ge}$ interfaces. <i>Applied Physics Express</i> , 2014, 7, 061301.	2.4	2
7	Influence of Ge substrate orientation on crystalline structures of $\text{Ge}_{1-x}\text{Sn}_x$ epitaxial layers. <i>Thin Solid Films</i> , 2014, 557, 159-163.	1.8	14
8	Influence of Sn incorporation and growth temperature on crystallinity of $\text{Ge}_{1-x}\text{Sn}_x$ layers heteroepitaxially grown on Ge(110) substrates. <i>Thin Solid Films</i> , 2013, 531, 504-508.	1.8	18
9	Epitaxial growth and anisotropic strain relaxation of $\text{Ge}_{1-x}\text{Sn}_x$ layers on Ge(110) substrates. <i>Solid-State Electronics</i> , 2013, 83, 71-75.	1.4	11
10	Crystallinity Improvement of Epitaxial Ge Grown on a Ge(110) Substrate by Incorporation of Sn. <i>Applied Physics Express</i> , 2012, 5, 015501.	2.4	14